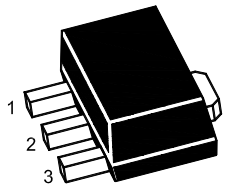
Plastic-Encapsulate Transistors

TRANSISTOR (PNP)



1.Base 2.Collector 3.Emitter

SOT-89 Plastic Package

FEATURE

- **High voltage**
- **Large continuous collector current capability**

MARKING: 1013

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-1	A
P_C	Collector Power Dissipation	0.5	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	250	℃/W

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

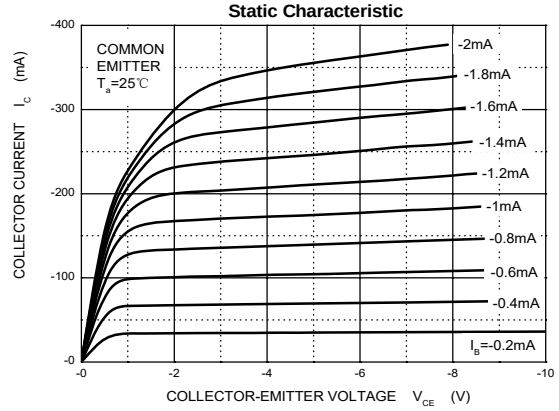
Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=- 100μA , I_E=0	-160		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -1mA , I_B=0	-160		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -10μA, I_C=0	-6		V
Collector cut-off current	I_{CBO}	V_{CB}=-150 V , I_E=0		-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-6V, I_C=0		-1	μA
DC current gain	h_{FE}	V_{CE}=-5 V, I_C=- 200mA	60	320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -500m A, I_B= -50mA		-1.5	V
Base-emitter voltage	V_{BE}	I_C= -5 mA, V_{CE}=- 5V		-0.75	V
Transition frequency	f_T	V_{CE}= -5 V, I_C= -200mA	15		MHz

CLASSIFICATION OF h_{FE}

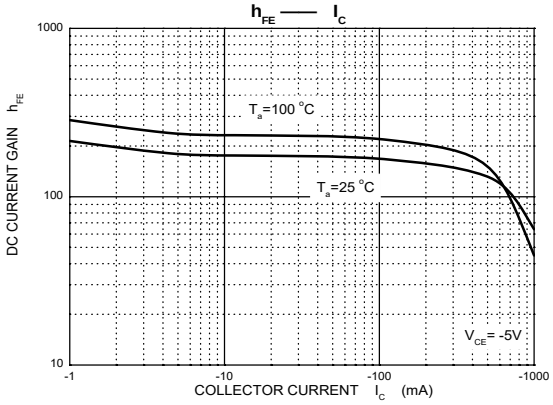
Rank	R	O	Y
Range	60-120	100-200	160-320

Typical Characteristics

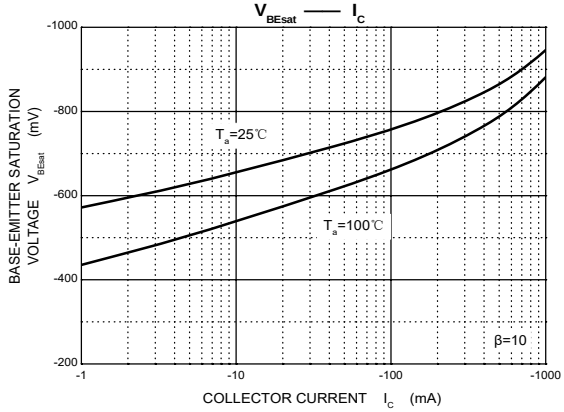
Static Characteristic



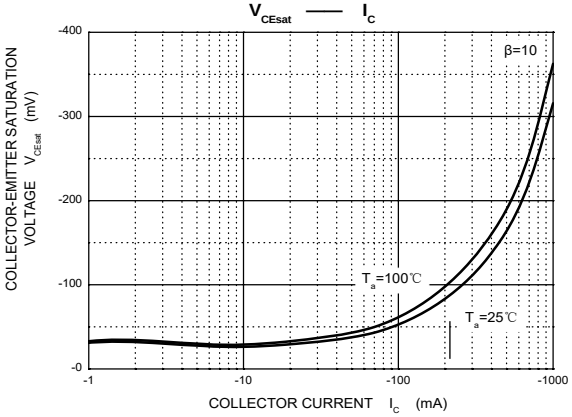
h_{FE} —— I_C



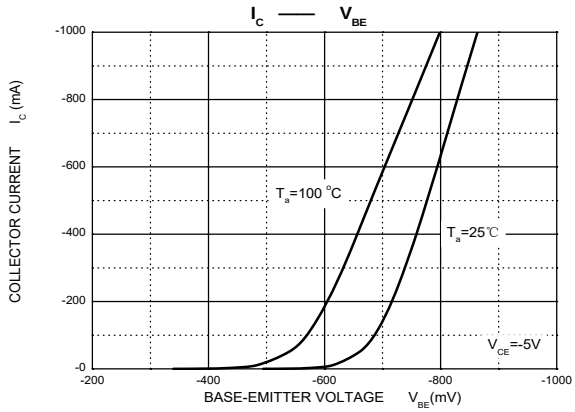
V_{BEsat} —— I_C



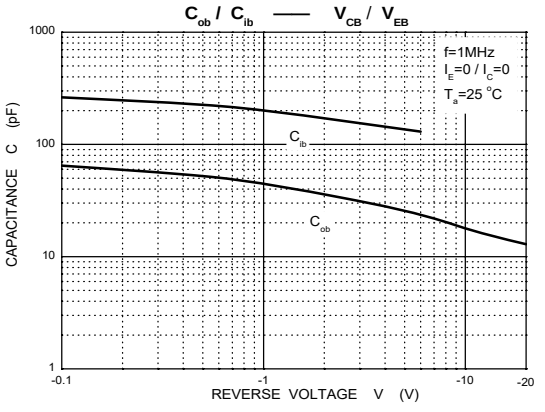
V_{CEsat} —— I_C



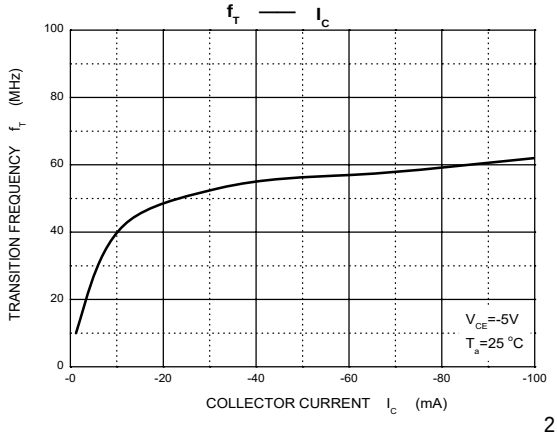
I_C —— V_{BE}



C_{ob} / C_{ib} —— V_{CB} / V_{EB}



f_T —— I_C



P_c —— T_a